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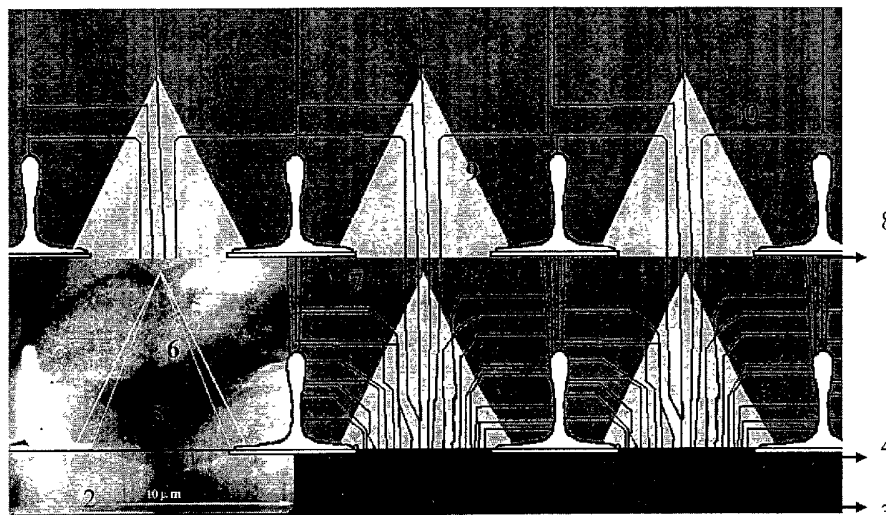
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[Continued on next page]

(54) Title: MANUFACTURING GALLIUM NITRIDE SUBSTRATES BY LATERAL OVERGROWTH THROUGH MASKS AND DEVICES FABRICATED THEREOF



(57) Abstract: Gallium nitride substrates are grown by epitaxial lateral overgrowth using multiple steps. On a masked substrate having openings areas, selective growth produces first triangular stripes in which most of the threading dislocations are bent at 90°. In a second step, growth conditions are changed to increase the lateral growth rate and produce a flat (0001) surface. At this stage the density of dislocations on the surface is $<5 \times 10^7 \text{ cm}^{-2}$. Dislocations are primarily located at the coalescence region between two laterally grown facets pinching off together. To further decrease the dislocation density a second masking step is achieved, with the openings exactly located above the first ones. Threading dislocations (TDs) of the coalescence region do not propagate in the top layer. Therefore the density of dislocations is lowered below $<1 \times 10^7 \text{ cm}^{-2}$ over the entire surface.

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Electronic data base consulted during the international search (name of data base and, where practical, search terms used) EPO-Internal, INSPEC		
C. DOCUMENTS CONSIDERED TO BE RELEVANT		
Category °	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
Y	EP 1 291 904 A (FUJI PHOTO FILM CO LTD) 12 March 2003 (2003-03-12) paragraphs '0019! - '0044!; figures 1-3 -----	1-26
Y	US 2003/062529 A1 (SUEHIRO YOSHINOBU ET AL) 3 April 2003 (2003-04-03) paragraph '0093! -----	1-26
Y	WO 02/099859 A (ASAI MAKOTO ; KATO HISAKI (JP); KANEYAMA NAOKI (JP); TOYODA GOSEI KK () 12 December 2002 (2002-12-12) third embodiment	1-26
P	-& EP 1 403 912 A (TOYODA GOSEI KK) 31 March 2004 (2004-03-31) paragraph '0046! ----- -/--	
<input checked="" type="checkbox"/>	Further documents are listed in the continuation of box C.	<input checked="" type="checkbox"/>
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International Application No

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C.(Continuation) DOCUMENTS CONSIDERED TO BE RELEVANT		
Category °	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
Y	BEAUMONT B ET AL.: "Mg-enhanced lateral overgrowth of GaN on patterned GaN/sapphire substrate by selective metal organic vapour phase epitaxy" MRS INTERNET JOURNAL OF NITRIDE SEMICONDUCTOR RESEARCH, vol. 3, 1998, XP001203903 page 3, right-hand column, paragraphs 2,3 -----	1-26
A	WO 01/80311 A (UNIV VIRGINIA COMMONWEALTH) 25 October 2001 (2001-10-25) figure 12 -----	1-26
A	US 2001/039104 A1 (ITO SHINGETOSHI ET AL) 8 November 2001 (2001-11-08) paragraphs '0113! - '0128! -----	1-26
A	US 2003/032288 A1 (KOZAKI TOKUYA ET AL) 13 February 2003 (2003-02-13) figure 2 -----	1-26

INTERNATIONAL SEARCH REPORT

Information on patent family members

International Application No
PCT/IB2004/001914

Patent document cited in search report	Publication date	Patent family member(s)	Publication date
EP 1291904 A	12-03-2003	EP 1291904 A2	12-03-2003
		JP 2004026624 A	29-01-2004
		US 2003047746 A1	13-03-2003
US 2003062529 A1	03-04-2003	JP 2003110136 A	11-04-2003
		EP 1263058 A2	04-12-2002
		US 2003122478 A1	03-07-2003
WO 02099859 A	12-12-2002	JP 2002367908 A	20-12-2002
		JP 2003068662 A	07-03-2003
		EP 1403912 A1	31-03-2004
		WO 02099859 A1	12-12-2002
		TW 550709 B	01-09-2003
		US 2004169192 A1	02-09-2004
		TW 548696 B	21-08-2003
EP 1403912 A	31-03-2004	JP 2002367908 A	20-12-2002
		JP 2003068662 A	07-03-2003
		EP 1403912 A1	31-03-2004
		US 2004169192 A1	02-09-2004
		WO 02099859 A1	12-12-2002
		TW 550709 B	01-09-2003
		TW 548696 B	21-08-2003
WO 0180311 A	25-10-2001	AU 7481001 A	30-10-2001
		WO 0180311 A1	25-10-2001
		US 2002013042 A1	31-01-2002
US 2001039104 A1	08-11-2001	JP 11297630 A	29-10-1999
		US 2002098641 A1	25-07-2002
		US 6294440 B1	25-09-2001
		JP 2000174343 A	23-06-2000
US 2003032288 A1	13-02-2003	AU 7454501 A	02-01-2002
		CA 2412999 A1	27-12-2001
		CN 1441982 T	10-09-2003
		EP 1320870 A2	25-06-2003
		WO 0199155 A2	27-12-2001
		JP 2002261032 A	13-09-2002
		TW 508841 B	01-11-2002
		US 2003160232 A1	28-08-2003
		US 2001053618 A1	20-12-2001